



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

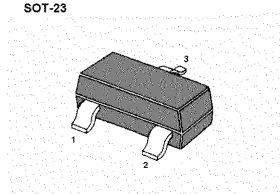
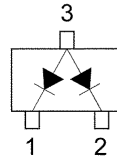
TEL: 852-2790 0314 FAX: 852-2790 0206

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SILICON EPITAXIAL PLANAR DIODE

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



Marking Code: **A3**
SOT-23 Plastic Package

Applications

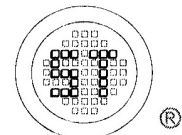
Ultra high speed switching application

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Maximum Peak Forward Current	I _{FM}	300	mA
Surge Current (10ms)	I _{FSM}	2	A
Average Forward Current	I _O	100	mA
Power Dissipation	P _{tot}	150	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _s	-55 to +125	°C

Characteristics at T_a = 25°C

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	I _F = 1mA	V _F	-	0.61	-	V
	I _F = 10mA	V _F	-	0.74	-	V
	I _F = 100mA	V _F	-	0.92	1.2	V
Reverse Current	V _R = 30V	I _R	-	-	0.1	μA
	V _R = 80V	I _R	-	-	0.5	μA
Total Capacitance	V _R = 0, f = 1MHz	C _T	-	2.2	4	pF
Reverse Recovery Time	I _F = 10mA	t _{rr}	-	1.6	4	ns



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Dated : 19/10/2005



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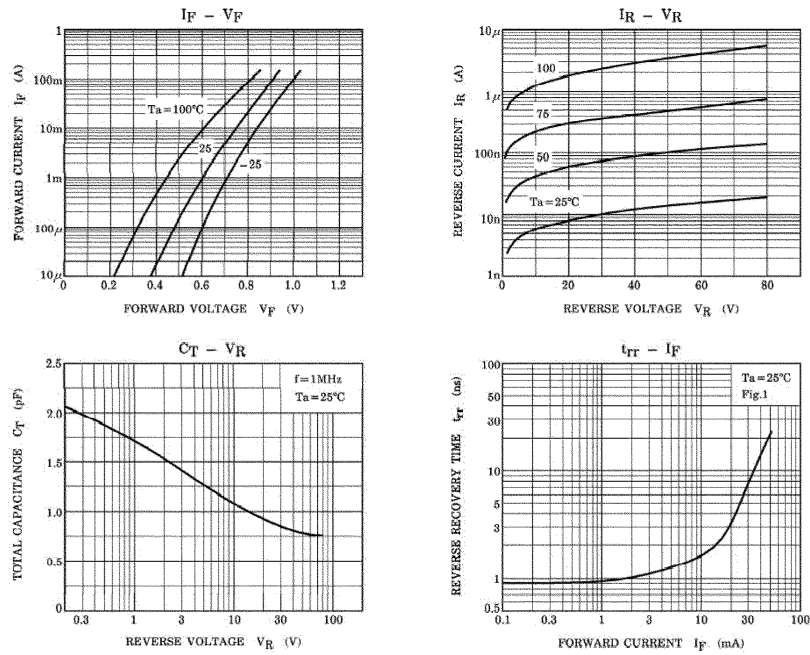
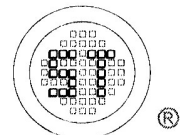
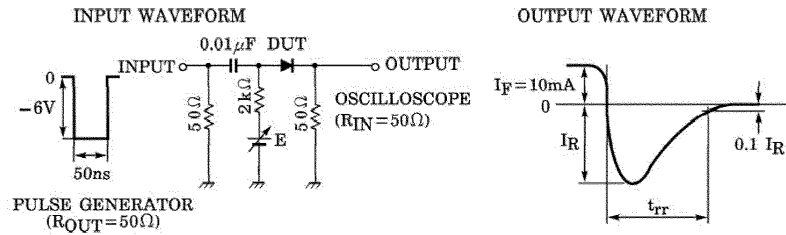


Fig.1 Reverse recovery time (t_{rr}) test circuit



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